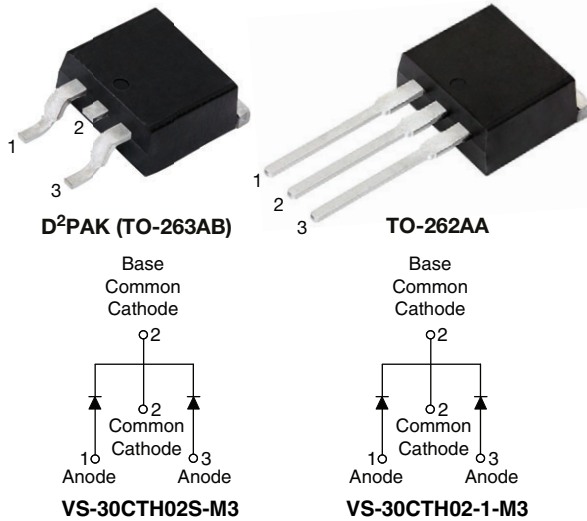


Hyperfast Rectifier, 30 A FRED Pt[®]



FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 200 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	2 x 15 A
V_R	200 V
V_F at I_F	0.78 V
t_{rr} typ.	30 ns
T_J max.	175 °C
Package	D ² PAK (TO-263AB), TO-262AA
Circuit configuration	Common cathode

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	$I_{F(AV)}$	$T_C = 159\text{ °C}$	15	A
			30	
Non-repetitive peak surge current	I_{FSM}	$T_C = 25\text{ °C}$	200	
Operating junction and storage temperatures	T_J, T_{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\ \mu\text{A}$	200	-	-	V
Forward voltage	V_F	$I_F = 15\text{ A}$	-	0.92	1.05	V
		$I_F = 15\text{ A}, T_J = 125\text{ °C}$	-	0.78	0.85	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	10	μA
		$T_J = 125\text{ °C}, V_R = V_R$ rated	-	5	300	
Junction capacitance	C_T	$V_R = 200\text{ V}$	-	57	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8	-	nH



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	t _{rr}	I _F = 1 A, di _F /dt = 50 A/μs, V _R = 30 V	-	-	35	ns	
		I _F = 1 A, di _F /dt = 100 A/μs, V _R = 30 V	-	-	30		
		T _J = 25 °C	I _F = 15 A di _F /dt = 200 A/μs V _R = 160 V	-	26		-
		T _J = 125 °C		-	40		-
Peak recovery current	I _{RRM}	T _J = 25 °C	-	2.8	-	A	
		T _J = 125 °C	-	6.0	-		
Reverse recovery charge	Q _{rr}	T _J = 25 °C	-	37	-	nC	
		T _J = 125 °C	-	120	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}	-65	-	175	°C	
Thermal resistance, junction to case per diode	R _{thJC}	-	-	1.1	°C/W	
Weight		-	2.0	-	g	
		-	0.07	-	oz.	
Mounting torque		6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D ² PAK (TO-263AB)			30CTH02S	
		Case style TO-262			30CTH02-1	

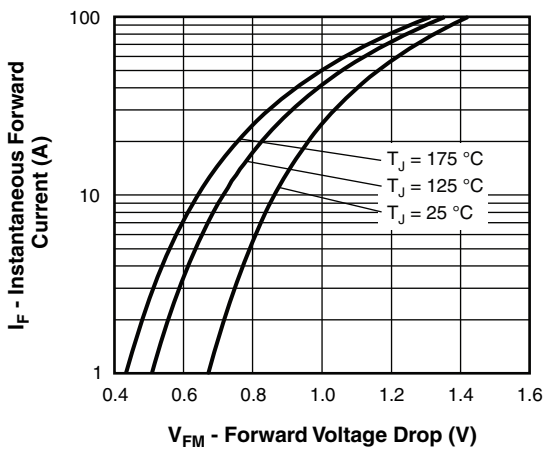


Fig. 1 - Maximum Forward Voltage Drop Characteristics

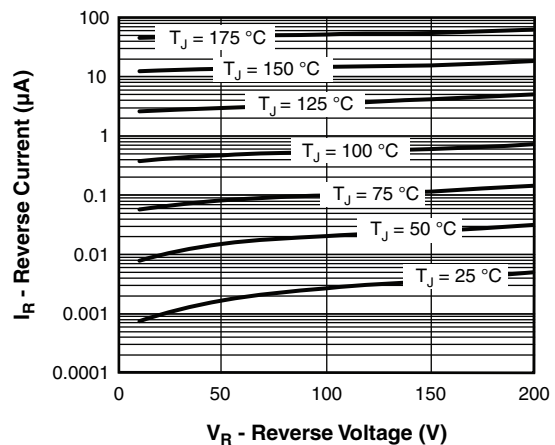


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

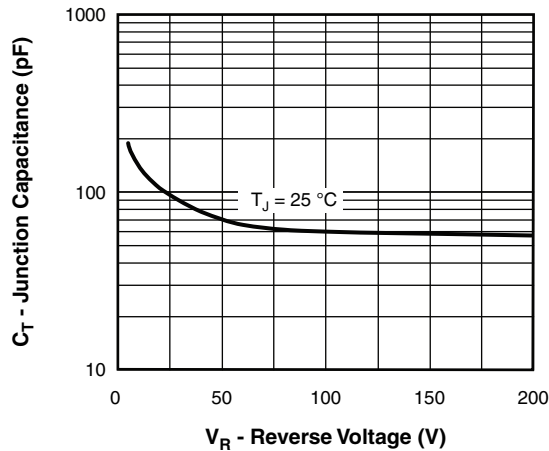


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

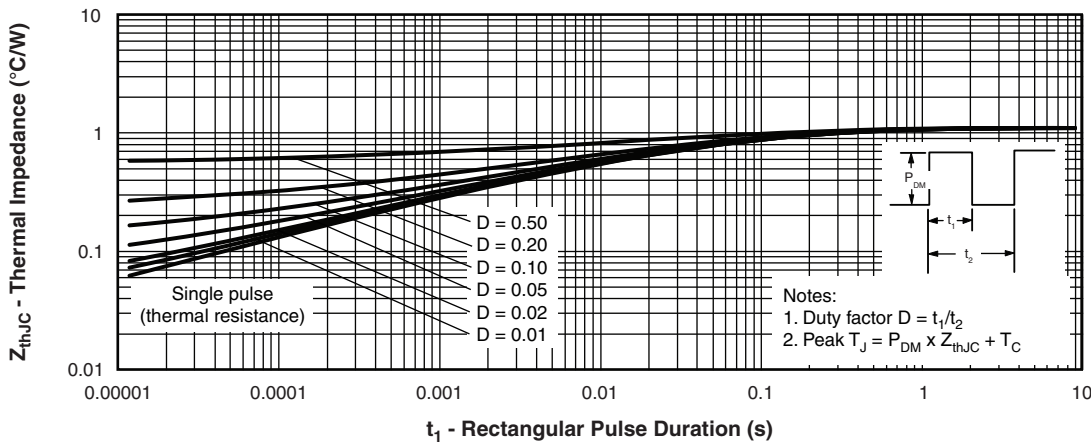


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

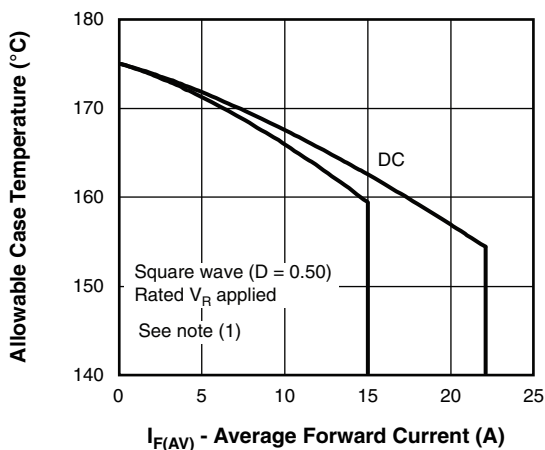


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

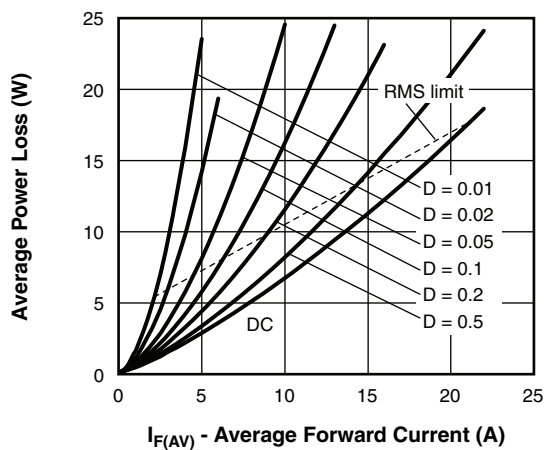


Fig. 6 - Forward Power Loss Characteristics

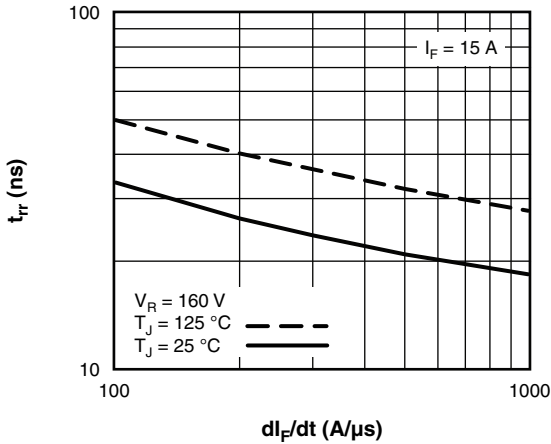


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

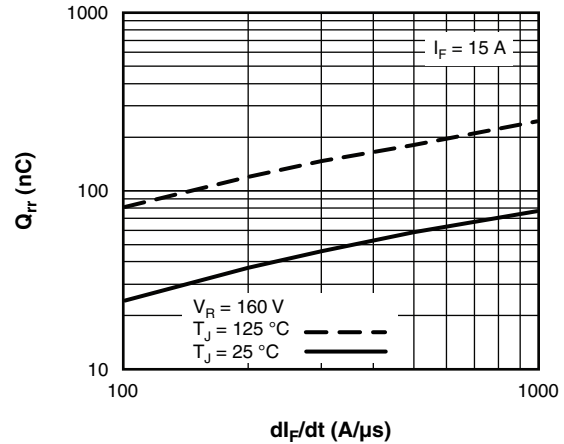
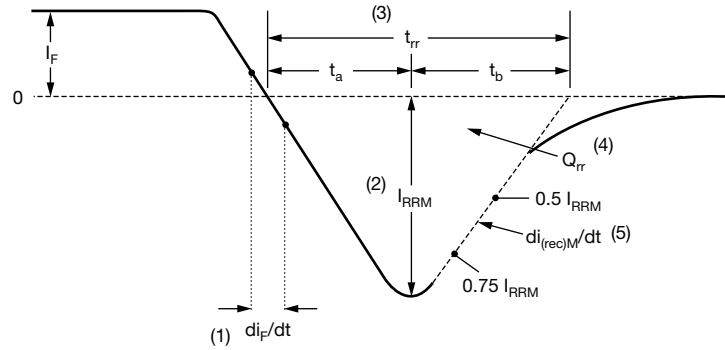


Fig. 8 - Typical Stored Charge vs. di_F/dt

Note

- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
 Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R



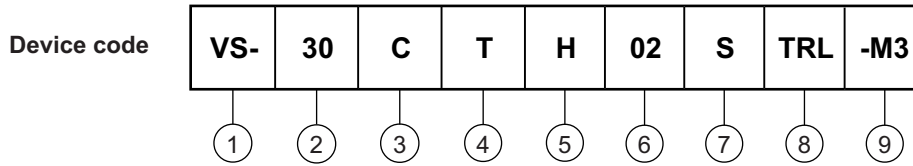
- (1) di_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Current rating (30 A)
- 3** - C = common cathode
- 4** - T = TO-220, D²PAK
- 5** - H = hyperfast rectifier
- 6** - Voltage rating (02 = 200 V)
- 7** -
 - S = D²PAK
 - -1 = TO-262
- 8** -
 - None = tube (50 pieces)
 - TRL = tape and reel (left oriented, for D²PAK package)
 - TRR = tape and reel (right oriented, for D²PAK package)
- 9** - Environmental digit:
 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

LINKS TO RELATED DOCUMENTS		
Dimensions	D ² PAK	www.vishay.com/doc?96164
	TO-262AA	www.vishay.com/doc?96165
Part marking information	D ² PAK	www.vishay.com/doc?95444
	TO-262AA	www.vishay.com/doc?95443
Packaging information		www.vishay.com/doc?96424

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC® outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB



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